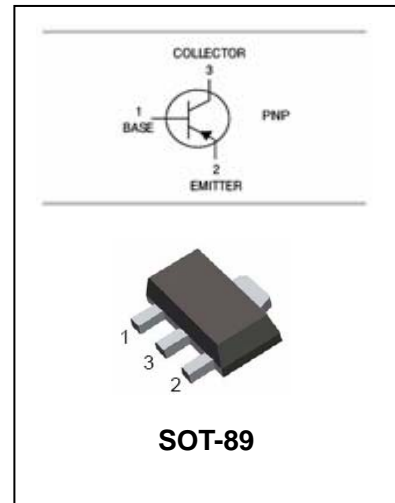


PNP Silicon Epitaxial Planar Transistor

KTA1664

FEATURES

- 1W(Mounted on Ceramic Substrate).
- Small flat package.
- Complementary: KTC4376.



ORDERING INFORMATION

Type No.	Marking	Package Code
KTA1664	RO/RV	SOT-89

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	-35	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.8	A
I _B	Base Current	-0.16	A
P _C	Collector Dissipation	500	mW
T _j , T _{stg}	Junction and Storage Temperature	-55 to +150	°C



PNP Silicon Epitaxial Planar Transistor

KTA1664

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1mA, I_E=0$	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1mA, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-35V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-1V, I_C=-100mA$	100		320	
		$V_{CE}=-1V, I_C=-700mA$	35			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-20mA$			-0.7	V
Base-emitter voltage	V_{BE}	$V_{CE}=-1V, I_C=-10mA$	-0.5		-0.8	V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-10mA$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		19		pF

CLASSIFICATION OF $h_{FE(1)}$

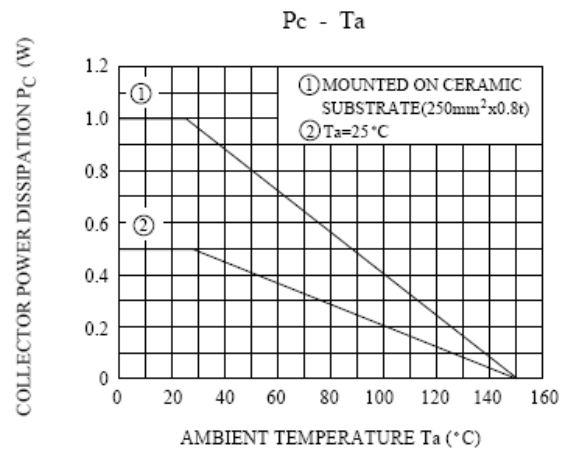
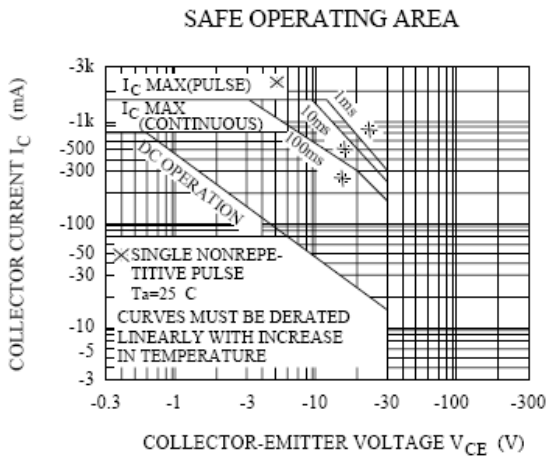
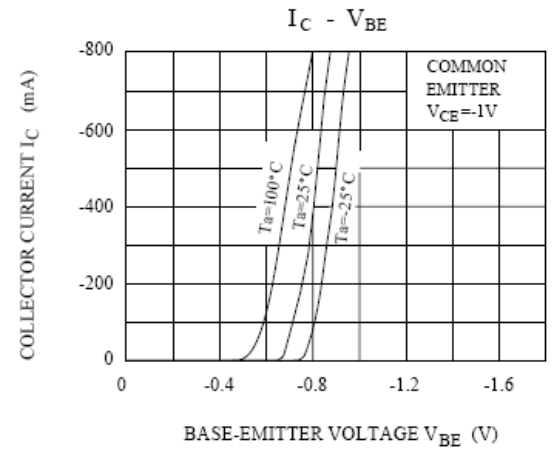
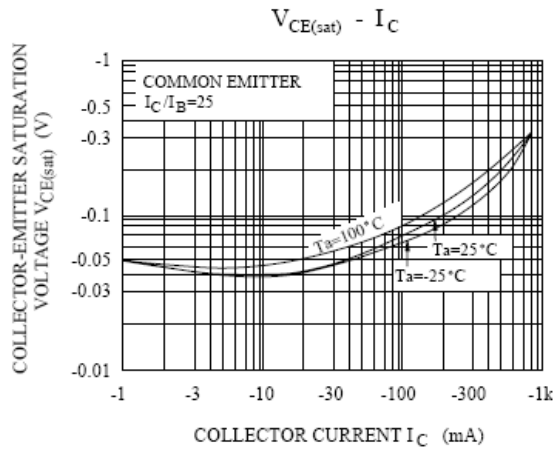
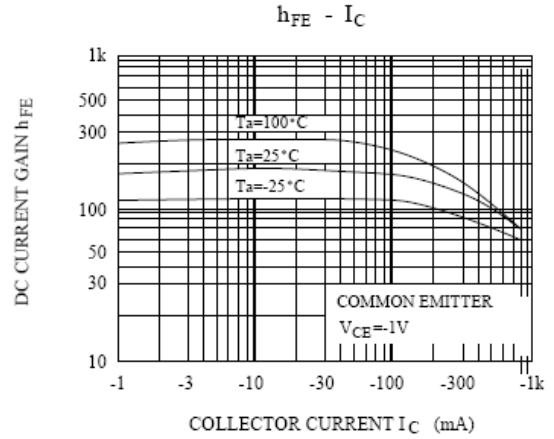
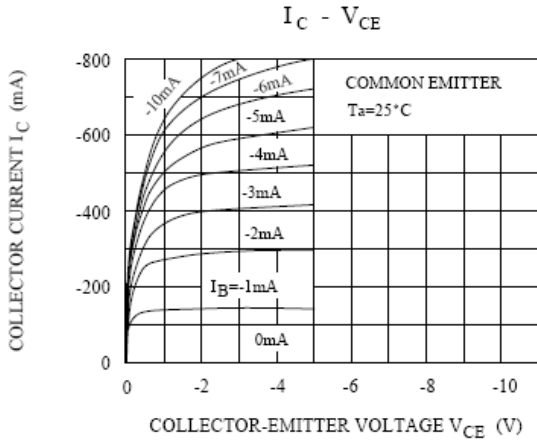
Rank	O	Y
Range	100-200	160-320
MARKING	RO	RY



PNP Silicon Epitaxial Planar Transistor

KTA1664

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



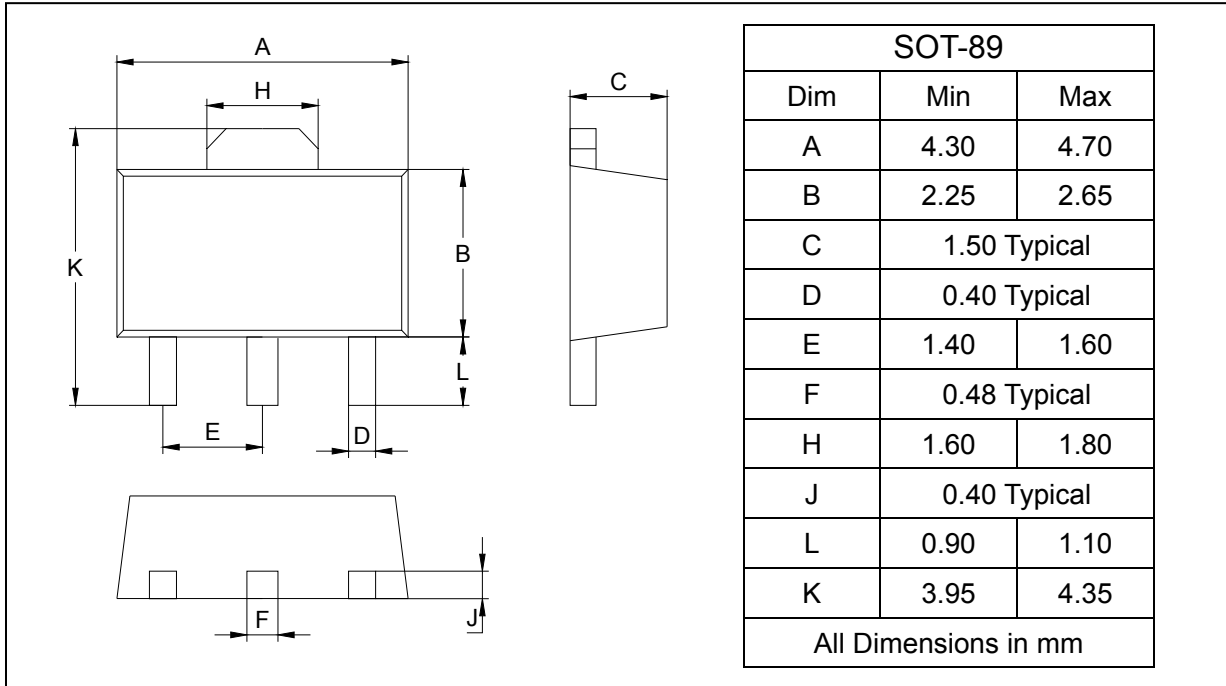
PNP Silicon Epitaxial Planar Transistor

KTA1664

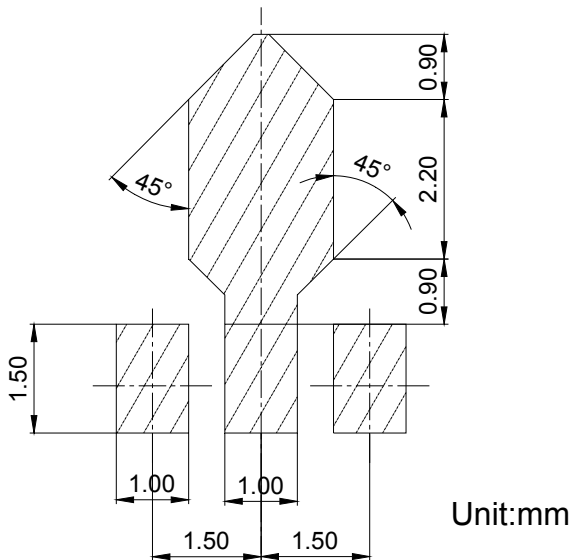
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
KTA1664	SOT-89	1000/Tape&Reel